

MPFF450R12MBF

1200V 450A IGBT Module

Electrical Features

- Trench/Fieldstop IGBT
- Low $V_{CE}(sat)$
- $V_{CE}(sat)$ with positive temperature coefficient
- $10 \ \mu \ s$ short circuit capability
- Fast&soft reverse recovery anti-parallel FWD
- Low inductance case



Typical Applications

- Motor Drives
- UPS System
- Servo Drives
- Wind Turbines

IGBT, Inverter

Maximu	ım Rated Values						
Symbol	Item	Conditions			Rating		Unit
IGBT							
V _{CES}	Collector-emitter voltage	T _{vj} =25°C			1200		V
V _{GES}	Gate-emitter voltage	-			±20		V
Ic	Collector current, DC	T _C =100°C,T _{vj} =175°C			450		Α
I _{CRM}	Repetitive peak collector current	t _p =1ms			90	900	
t_{SC}	Short circuit withstand time	V_{GE} =15V, V_{CC} =600V, T_{vj} ≤150°C			1	10	
P _{tot}	Total power dissipation	$T_{C}=25^{\circ}C, T_{vj}=175^{\circ}C$			2586		W
Charact	teristics Values						
Symbol	Item	Conditions			Values		Unit
IGBT				Min.	Тур.	Max.	
ICES	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$		-	-	10	μA
I _{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$		-	-	50	nA
V _{GE(th)}	Gate-emitter threshold voltage	$I_C=17.1$ mA, $V_{CE}=V_{GE}$, $T_{vj}=25$ °C		5.0	5.7	7.0	
		I _C =450A	T _{vj} =25°C	-	2.13	2.5	v
V _{CEsat}	Collector-emitter saturation voltage	$T_{c}=430 \text{A}$ $V_{GE}=15 \text{V}$ $T_{vj}=125^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$	T _{vj} =125°C	-	2.60	-	
			T _{vj} =150°C	-	2.68	-	
Cies	Input capacitance	V -25VV -0V		-	31.8	-	
C _{oes}	Output capacitance	$V_{CE}=25V, V_{GE}=0V$ f=1MHz, T _{vj} =25°C $V_{GE}=\pm 15V$		-	2.1	-	nF
C _{res}	Reverse transfer capacitance			-	1.08	-	
Q _G	Gate charge			-	2814	-	nC
Rg	Internal gate resistance	T _{vj} =25°C		-	0.4	-	Ω

			T _{vj} =25°C	-	147	-	
$t_{d(on)}$	Turn-on delay time		T _{vj} =125°C	-	148	-	
			T _{vj} =150°C	-	152	-	
		V _{CC} =600V	T _{vj} =25°C	-	158	-	
tr	Rise time	Ic=450A	T _{vj} =125°C	-	172	-	
		$V_{GE}=\pm 15V$	T _{vj} =150°C	-	181	-	na
		$R_{G(on)}=5.1 \Omega$	T _{vj} =25°C	-	557	-	ns
$t_{d(off)}$	Turn-off delay time	$R_{G(off)}=5.1 \Omega$	T _{vj} =125°C	-	648	-	
		L _{load} =50uH	T _{vj} =150°C	-	665	-	
			T _{vj} =25°C	-	90	-	
t_{f}	Fall time		T _{vj} =125°C	-	160	-	
			T _{vj} =150°C	-	185	-	
		V _{CC} =600V, I _C =450A	T _{vj} =25°C	-	64.5	-	
Eon	Turn-on energy (per pulse)	$V_{GE}=\pm 15V$, $R_{G(on)}=5.1\Omega$	T _{vj} =125°C	-	92.5	-	
		di/dt=3800A/µs(T _{vj} =150°C)	T _{vj} =150°C	-	99.1	-	T
		V _{CC} =600V, I _C =450A	T _{vj} =25°C	-	36.8	-	mJ
E_{off}	Turn-off energy (per pulse)	$V_{GE}=\pm 15V$, $R_{G(off)}=5.1\Omega$	T _{vj} =125°C	-	48.3	-	1
		$du/dt=6230V/\mu s(T_{vj}=150^{\circ}C)$	T _{vj} =150°C	-	50.9	-	
00.1	Short-circuit current	$V_{CC}=600V, V_{GE} \le 15V, T_{vj}=25^{\circ}$	C		2200		
SC data		$V_{CES} \le 1200 V, t_P \le 10 \mu s$			2388	-	A
R _{thJC}	Thermal resistance, junction to case	per IGBT		-	-	0.058	K/W
R_{thCH}	Thermalresistance, case to heatsink	per IGBT/ λgrease=1W/(m·H	K)	-	0.03	-	K/W
T _{vjop}	Tanan anatana an dan amitahing aga dit	•		40			
⊥ vjop	Temperature under switching condit	ions		-40		150	°C
	Inverter	10NS		-40		150	°C
Diode,	· · ·	ions		-40		150	°C
Diode,	Inverter	Condition	15	-40	Rat	150 ting	°C Unit
Diode, Maximu	Inverter um Rated Values	1	15	-40			
Diode, Maximu Symbol	Inverter um Rated Values Item	Condition	15		12	ting	Unit
Diode, Maximu Symbol V _{RRM}	Inverter um Rated Values Item Repetitive peak reverse voltage	Condition T _{vj} =25°C	15		12 45	ting 00	Unit V
Diode, Maximu Symbol V _{RRM} I _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC	Condition T _{vj} =25°C T _C =100°C,T _{vj} =150°C	15		12 45 90	ting 00 50	Unit V A
Diode, Maximu Symbol V _{RRM} I _F I _{FRM} I ² t	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current	$\begin{tabular}{ c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_{C}=100°C, T_{vj}=150°C \\ \hline t_{p}=1ms \\ \hline \end{tabular}$	15		12 45 90	ting 00 50 00	Unit V A A
Diode, Maximu Symbol V _{RRM} I _F I _{FRM} I ² t	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value	Condition $T_{vj}=25$ °C $T_{C}=100$ °C, $T_{vj}=150$ °C $t_{p}=1ms$ $V_{R}=0V,t_{p}=10ms,T_{vj}=150$ °C	15 T _{vj} =25°C	-40	12 45 90	ting 00 50 00	Unit V A A
Diode, Maximu Symbol V _{RRM} I _F I _{FRM} I ² t	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value	$\begin{tabular}{ c c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_{C}=100°C, T_{vj}=150°C \\ \hline t_{p}=1ms \\ V_{R}=0V, t_{p}=10ms, T_{vj}=150°C \\ \hline I_{F}=450A \\ \hline \end{tabular}$			12 45 90 285	ting 00 50 00 500	Unit V A A
Diode, Maximu Symbol V _{RRM} I _F I _{FRM} I ² t Charact	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values	Condition $T_{vj}=25$ °C $T_{C}=100$ °C, $T_{vj}=150$ °C $t_{p}=1ms$ $V_{R}=0V,t_{p}=10ms,T_{vj}=150$ °C	T _{vj} =25°C		12 45 90 285 2.19	ting 00 50 00 500 2.5	Unit V A A A ² s
Diode, Maximu Symbol V _{RRM} I _F I _{FRM} I ² t Charact	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values	$\begin{tabular}{ c c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_{C}=100°C, T_{vj}=150°C \\ \hline t_{p}=1ms \\ V_{R}=0V, t_{p}=10ms, T_{vj}=150°C \\ \hline I_{F}=450A \\ \hline \end{tabular}$	T _{vj} =25°C T _{vj} =125°C	- -	12 45 90 285 2.19 2.08	ting 00 50 00 500 2.5 -	Unit V A A A ² s
Diode, Maximu Symbol V _{RRM} I _F I _{FRM} I ² t Charact	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values	$\begin{tabular}{ c c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_{C}=100°C, T_{vj}=150°C \\ \hline t_{p}=1ms \\ V_{R}=0V, t_{p}=10ms, T_{vj}=150°C \\ \hline I_{F}=450A \\ \hline \end{tabular}$	Tvj=25°C Tvj=125°C Tvj=150°C	- -	12 45 90 285 2.19 2.08 2.02	ting 00 50 00 500 2.5 -	Unit V A A A ² s
Diode, Maximu Symbol V _{RRM} IF IFRM I ² t Charact V _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values Continuous forward voltage	$\begin{tabular}{ c c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_{C}=100°C, T_{vj}=150°C \\ \hline t_{p}=1ms \\ V_{R}=0V, t_{p}=10ms, T_{vj}=150°C \\ \hline I_{F}=450A \\ \hline \end{tabular}$	Tvj=25°C Tvj=125°C Tvj=150°C Tvj=25°C	- - - -	12 45 90 285 2.19 2.08 2.02 183	ting 00 50 00 500 2.5 - - -	Unit V A A A ² s
Diode, Maximu Symbol V _{RRM} IF IFRM I ² t Charact V _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values Continuous forward voltage	$\begin{tabular}{ c c c c c } \hline Condition \\ \hline T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=150^{\circ}C \\ \hline t_{p}=1ms \\ \hline V_{R}=0V, t_{p}=10ms, T_{vj}=150^{\circ}C \\ \hline I_{F}=450A \\ \hline V_{GE}=0V \\ \hline \end{tabular}$	Tvj=25°C Tvj=125°C Tvj=150°C Tvj=25°C Tvj=125°C	- - - - -	12 45 90 285 2.19 2.08 2.02 183 259	ting 00 50 00 500 2.5 - - - - -	Unit V A A A ² s
Diode, Maximu Symbol V _{RRM} IF IFRM I ² t Charact V _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values Continuous forward voltage	$\begin{tabular}{ c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_C=100°C, T_{vj}=150°C \\ \hline t_p=1ms \\ V_R=0V, t_p=10ms, T_{vj}=150°C \\ \hline I_F=450A \\ V_{GE}=0V \\ \hline V_R=600V \\ \hline \end{tabular}$	$\begin{array}{c} T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=150^{\circ}C\\ T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=150^{\circ}C\\ \end{array}$	- - - - -	12 4 90 28 2.19 2.08 2.02 183 259 290	ting 00 50 00 500 2.5 - - - - -	Unit V A A A ² s
Diode, Maximu Symbol V _{RRM} IF IFRM I ² t Charact V _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values Continuous forward voltage Peak reverse recovery current	$\begin{tabular}{ c c c c c } \hline Condition \\ \hline T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=150^{\circ}C \\ \hline t_{p}=1ms \\ \hline V_{R}=0V, t_{p}=10ms, T_{vj}=150^{\circ}C \\ \hline I_{F}=450A \\ \hline V_{GE}=0V \\ \hline V_{R}=600V \\ \hline I_{F}=450A \\ \hline \end{array}$	$\begin{array}{c} T_{vj} = 25 ^{\circ}\text{C} \\ T_{vj} = 125 ^{\circ}\text{C} \\ T_{vj} = 150 ^{\circ}\text{C} \\ T_{vj} = 25 ^{\circ}\text{C} \\ T_{vj} = 125 ^{\circ}\text{C} \\ T_{vj} = 150 ^{\circ}\text{C} \\ T_{vj} = 25 ^{\circ}\text{C} \\ \end{array}$	- - - - - - - - -	12 4 90 285 2.19 2.08 2.02 183 259 290 175	ting 00 50 00 500 2.5 - - - - - - - -	Unit V A A ² s V
Diode, Maximu Symbol V _{RRM} IF IFRM I ² t Charact V _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values Continuous forward voltage Peak reverse recovery current	$\begin{tabular}{ c c c c } \hline Condition \\ \hline T_{vj}=25°C \\ \hline T_C=100°C, T_{vj}=150°C \\ \hline t_p=1ms \\ V_R=0V, t_p=10ms, T_{vj}=150°C \\ \hline I_F=450A \\ V_{GE}=0V \\ \hline V_R=600V \\ I_F=450A \\ V_{GE}=-15V \\ \hline \end{tabular}$	$\begin{array}{c} T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=150^{\circ}C\\ T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=150^{\circ}C\\ T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=125^{\circ}C\\ \end{array}$	- - - - - - - - - - -	12 4 90 28 2.19 2.08 2.02 183 259 290 175 421	ting 00 50 500 500 2.5 - - - - - - - - - - - - -	Unit V A A ² s V
Diode, Maximu Symbol V _{RRM} IF IFRM I ² t Charact V _F	Inverter um Rated Values Item Repetitive peak reverse voltage Forward current,DC Repetitive peak forward current I ² t-value teristic Values Continuous forward voltage Peak reverse recovery current	$\begin{tabular}{ c c c c } \hline Condition \\ \hline T_{vj}=25^{\circ}C \\ \hline T_{C}=100^{\circ}C, T_{vj}=150^{\circ}C \\ \hline t_{p}=1ms \\ \hline V_{R}=0V, t_{p}=10ms, T_{vj}=150^{\circ}C \\ \hline V_{R}=0V, t_{p}=10ms, T_{vj}=10ms, T_{vj}$	$\begin{array}{c} T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=150^{\circ}C\\ T_{vj}=25^{\circ}C\\ T_{vj}=150^{\circ}C\\ T_{vj}=150^{\circ}C\\ T_{vj}=25^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=125^{\circ}C\\ T_{vj}=150^{\circ}C\\ \end{array}$	- - - - - - - - - - - - - - - -	12 4 90 285 2.19 2.08 2.02 183 259 290 175 421 657	ting 00 50 00 500 2.5 - - - - - - - - - - - - - -	Unit V A A ² s V

MPFF450R12MBF

Erec	Reverse recovery energy		T _{vj} =25°C	-	8.36	-	
		T _{vj} =125°C T _{vj} =150°C	-	20.2	-	mJ	
			T _{vj} =150°C	-	29.3	-	
R _{thJC}	Thermal resistance, junction to case	per diode		-	-	0.1	K/W
R _{thCH}	Thermalresistance, case to heatsink	per diode/ λ grease=1W/(m·K)		-	0.045	-	K/W
T _{vjop}	Temperature under switching conditions		-40		150	°C	

NTC Thermistor Characteristics

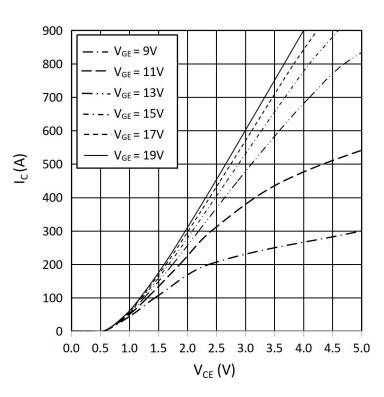
Symbol	Item	Conditions	Values			Unit
		Conditions	Min.	Тур.	Max.	
R ₂₅	Rated resistance	$T_{\rm C}=25^{\circ}{\rm C}$	-	5	-	kΩ
$\Delta R/R$	Deviation of resistance	$T_{C}=100^{\circ}C, R_{100}=493\Omega$	-5	-	5	%
P ₂₅	Power dissipation	$T_{\rm C}=25^{\circ}{\rm C}$	-	-	20	mW
B _{25/50}	B-constant	$R_2 = R_{25} exp[B_{25/50}(1/T_2-1/(298.15K))]$	-	3375	-	
B _{25/80}	B-constant	$R_2 = R_{25} exp[B_{25/80}(1/T_2-1/(298.15K))]$	-	3411	-	K
B _{25/100}	B-constant	$R_2 = R_{25} exp[B_{25/100}(1/T_2 - 1/(298.15K))]$	-	3433	-	

Module

Symbol	Item	Conditions	Rating			Unit
VISOL	Isolation voltage	Terminals to baseplate, RMS,f=50Hz,t=1min	2500			V
-	Material of module baseplate	-	Cu		-	
-	Internal isolation	Basic insulation(class 1, IEC 61140)	Al ₂ O ₃		-	
T _{stg}	Storage temperature	-	-40~125		°C	
Symbol	T.			Values		Unit
	Item	Conditions	Min.	Тур.	Max.	
М	Mounting torque for module mounting	Screw M6	3.0	-	5.0	Nm
	Terminal connection torque	Screw M6	2.5	-	5.0	Nm
ds	Creepage distance	Terminal to terminal	-	13	-	
		Terminal to base plate	-	14.5	-	mm
da		Terminal to terminal	-	10	-	
	Clearance	Terminal to base plate	-	12.5	-	mm
m	Weight	-	-	340	-	g

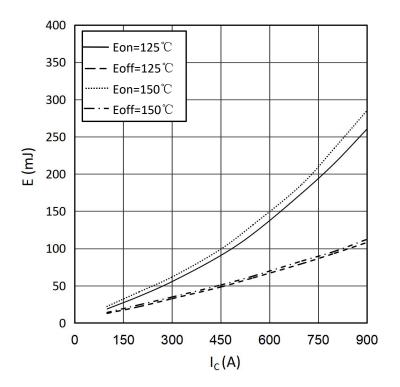
output characteristic IGBT, Inverter (typical)

 $I_{C} = f(V_{CE})$ $T_{vj} = 150^{\circ}C$



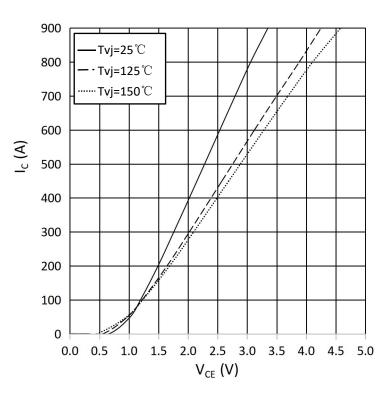


 $V_{GE} = \pm 15 V, R_{Gon} = 5.1 \Omega, R_{Goff} = 5.1 \Omega, V_{CE} = 600 V$



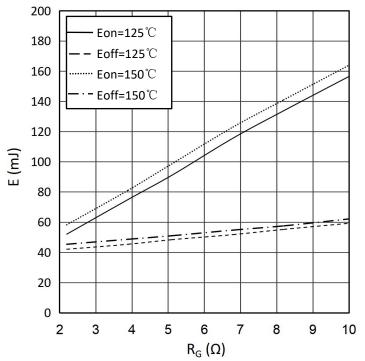
output characteristic IGBT, Inverter (typical)

 $I_{C} = f(V_{CE})$ $V_{GE} = 15 V$

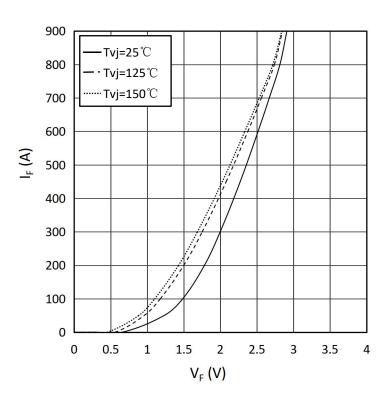


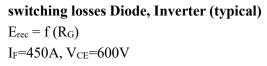
switching losses IGBT, Inverter(typical)

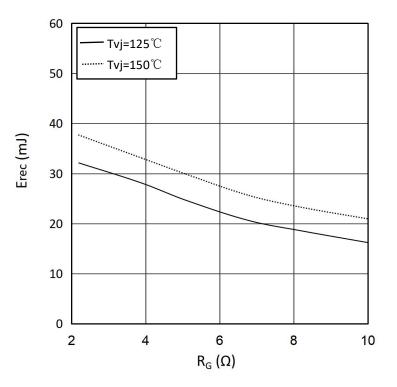
$$\begin{split} E_{\rm on} &= f\left(R_{\rm G}\right), \, E_{\rm off} = f\left(R_{\rm G}\right) \\ V_{\rm GE} &= \pm 15 \text{V}, \, I_{\rm C} = 450 \text{A}, \, V_{\rm CE} \text{=} \, 600 \text{V} \end{split}$$



forward characteristic of Diode, Inverter (typical) $I_F = f\left(V_F\right)$

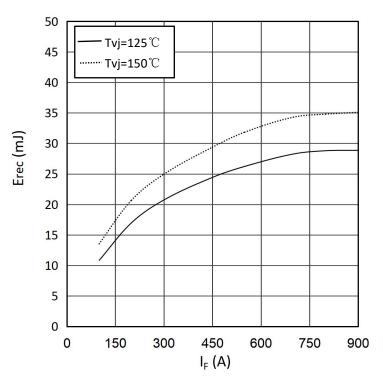




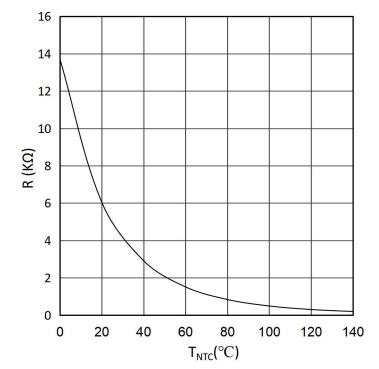


switching losses Diode, Inverter (typical)

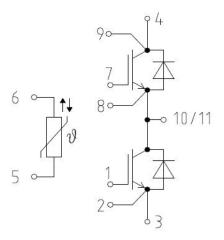
$$\begin{split} E_{rec} &= f\left(I_F\right) \\ R_{Gon} &= 5.1\Omega, \, V_{CE} &= 600V \end{split}$$



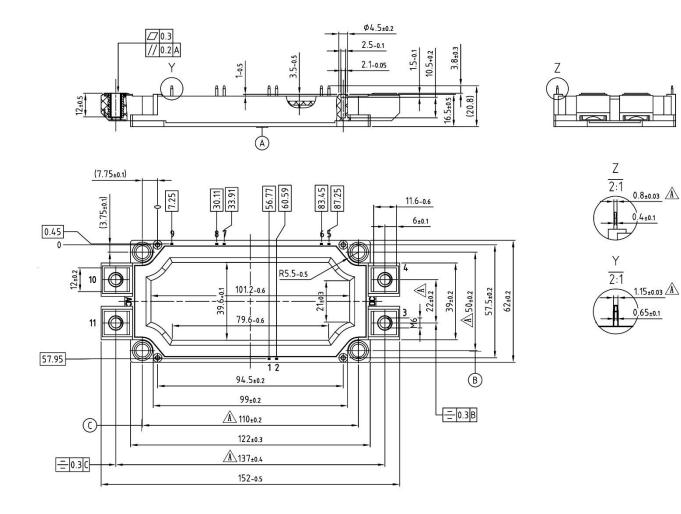
NTC-Thermistor-temperature characteristic(typical) R=f(T)



Circuit diagram headline







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